

Switching Fast SiC Cascode JFETs with a Snubber

AND90319/D

INTRODUCTION

The emergence of fast switching WBG devices has dramatically enhanced power density in a range of power conversion circuits such as active rectifiers, LLC bridges, phase shifted full bridges, and dual active bridges to name a few. These circuits form the backbone of efficient AC-DC and DC-DC stages in battery chargers for EVs, forklifts, solar inverters and power supplies, especially where power density is key. The fast switching enabled by these devices is best exploited in advanced packages such as TO247-4L, D2PAK-7L which have a Kelvin gate return. However, there are often supply-chain reasons why users are constrained to use standard packages like TO247-3L, TO220-3L and D2PAK-3L, which have high common source inductance.

onsemi has pioneered the introduction of SiC JFET based cascodes with easy drop in compatibility with Si MOSFETs, IGBTs as well as SiC MOSFETs, based on the 5 V threshold voltage and wide gate operating range of ± 25 V. These devices are inherently very fast switching, with excellent body diode characteristics. However, that also means that operating di/dts can be extremely high. To offer customers various options, the UJ3C series has been created with slower switching speeds, which has higher losses but is easier to use in older 3-leaded packages. Furthermore, a faster UF3C series is being introduced in packages with Kelvin gate returns, such as TO247-4L and D2PAK-7L that offer the highest level of switching performance. For customers that need to stay with standard three leaded packages such as TO247-3L, D2PAK-3L and TO220-3L, but still require lower losses in hard switched circuits than the UJ3C series, onsemi offers the UF3C series designed to be used with small RC snubbers to manage the high turn-off di/dts.

Wide-bandgap (WBG) FETs bring a new twist to the well-known RC snubber. Since the devices have very low output capacitance C_{oss} , relatively small values of snubber capacitance are shown to have a large impact on improving overshoots, suppressing gate oscillations and improving EMI. Snubber loss is measured and shown to be much smaller than $f \cdot CV^2$ [1] which is explained in the literature. As switching dV/dt increases, snubber losses increase, but it is also possible to use a smaller snubber to compensate.

In fact, it is found that a 3–5% increase in switching $E_{on} + E_{off}$ loss is enough to dramatically improve switching waveforms. The power loss in the snubber is therefore small enough for surface mount components rated for 0.25 W to 2 W. We also show that using a snubber simplifies the design effort in making the design compatible with many SiC switch manufacturers, and makes the designs, especially those in highly paralleled configurations, more tolerant of layout issues. The board space for such a snubber can be quite beneficial to ensure that EMI can be reduced at the source if needed, without forcing a major re-design and causing product release delays.

This application note presents the benefits of using an RC snubber connected between the drain and source of fast switching SiC devices in typical applications based on a half-bridge configuration. The challenge of suppressing excessive voltage overshoots and ringing noise is addressed. While the optimization of PCB layouts to reduce parasitic inductance can help, this may often not be possible due to board constraints or product release schedules. Moreover, the common approach to control switching speed from higher gate resistance increases switching loss and delay times. Therefore, this application note presents a practical solution using RC snubbers with fast switching SiC devices. The solution is verified by experimental double pulse tests (DPT) results. The snubber loss is measured very precisely, to assist users in computing the power rating of the snubber resistor. The beneficial impact of the snubber is analyzed for both hard switching and soft switching applications. This information has led to the creation of a simple user guide [2].

SNUBBER LOSS

A typical RC snubber configuration in a half-bridge is shown in Figure 1. It has a snubber capacitor (C_s) and a snubber resistor (R_s) in series. Load inductor L represents inductive load. The DC LINK capacitor has high capacitance to maintain DC bus voltage while providing energy to the load inductor L . C_d is the power loop decoupling capacitor, usually a ceramic capacitor. It is located close to the half-bridge to minimize power loop inductance during switching transients. CT is a current transformer.

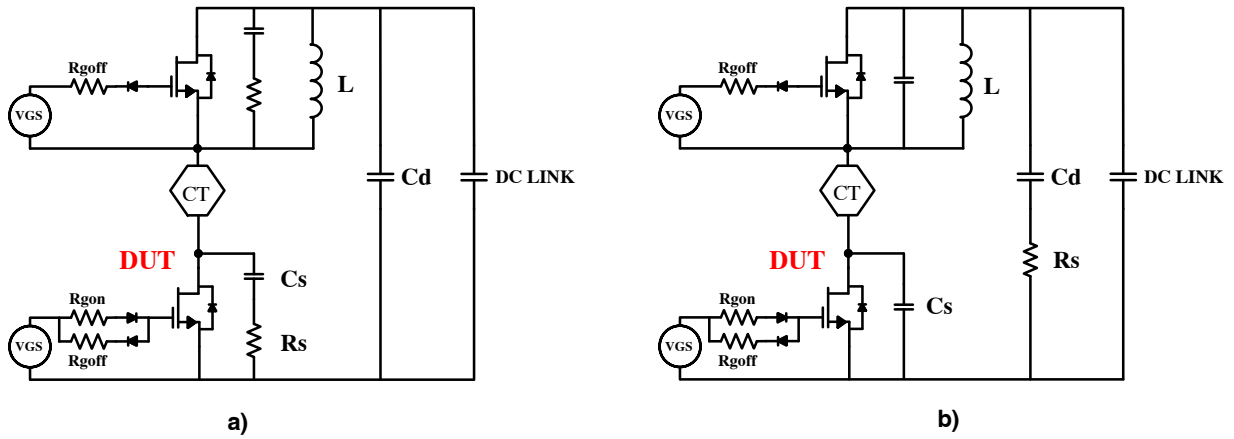


Figure 1. DPT Schematic with RC Snubbers on Both Switches for Hard Switching (a) and Soft Switching (b)

There are two major concerns with using a basic RC snubber. One is the extra switching energy loss. The other one is the power rating of the snubber resistor R_s . The Snubber C_s will introduce extra turn-on loss (E_{on}), while reducing turn-off loss (E_{off}). When the low side FET (DUT) in the double pulse circuit turns on, the displacement currents charging the high side C_s and discharging the low side C_s create additional loss in the DUT, which depends on the size of the capacitors C_s relative to the FET C_{oss} . During turn-off, as the dV/dt rises the C_s - R_s path diverts displacement current from the FET, reducing the switching loss in the FET.

Now if a snubber is not used, the SiC device needs to be substantially slowed down to prevent V_{DS} spikes and ringing during the turn-off transient. However, as shown in section Hard Switching Effect the UF3C120040K3S with snubber has the lowest overall loss. In other words, to reach high efficiency and dampen ringing, the increase of energy loss by switching faster FETs with a snubber is less than that of switching devices slower without a snubber. With a proper snubber design, high switching speed, high

efficiency and smooth waveforms can be simultaneously achieved.

For soft switching applications like LLC and PSFB the C_s energy is recycled during zero voltage switching (ZVS). Also, soft switching tends to have high switching frequencies. Therefore, a snubber R_s is not recommended. For supplying inductive loads with a half-bridge configuration like in Figure 1, the low side turn-off dV/dt will introduce a discharging current in high side snubber C_s which will reduce the low side turn-off current thus reducing E_{off} . Results in section Soft Switching Effect shows that C_s can help reducing turn-off loss (E_{off}).

Article [1] explains the difference of R_s loss calculation between ideal square V_{DS} waveforms and practical V_{DS} waveforms with a finite rise time. The common practice of $f \cdot CV^2$ overestimates the loss in a snubber resistor quite a lot. This is because in a practical V_{DS} waveform the snubber C_s is not charging or discharging at a constant voltage. The operating dV/dt has a strong effect on the accuracy of $f \cdot CV^2$ estimation, so it is best to measure snubber loss directly.

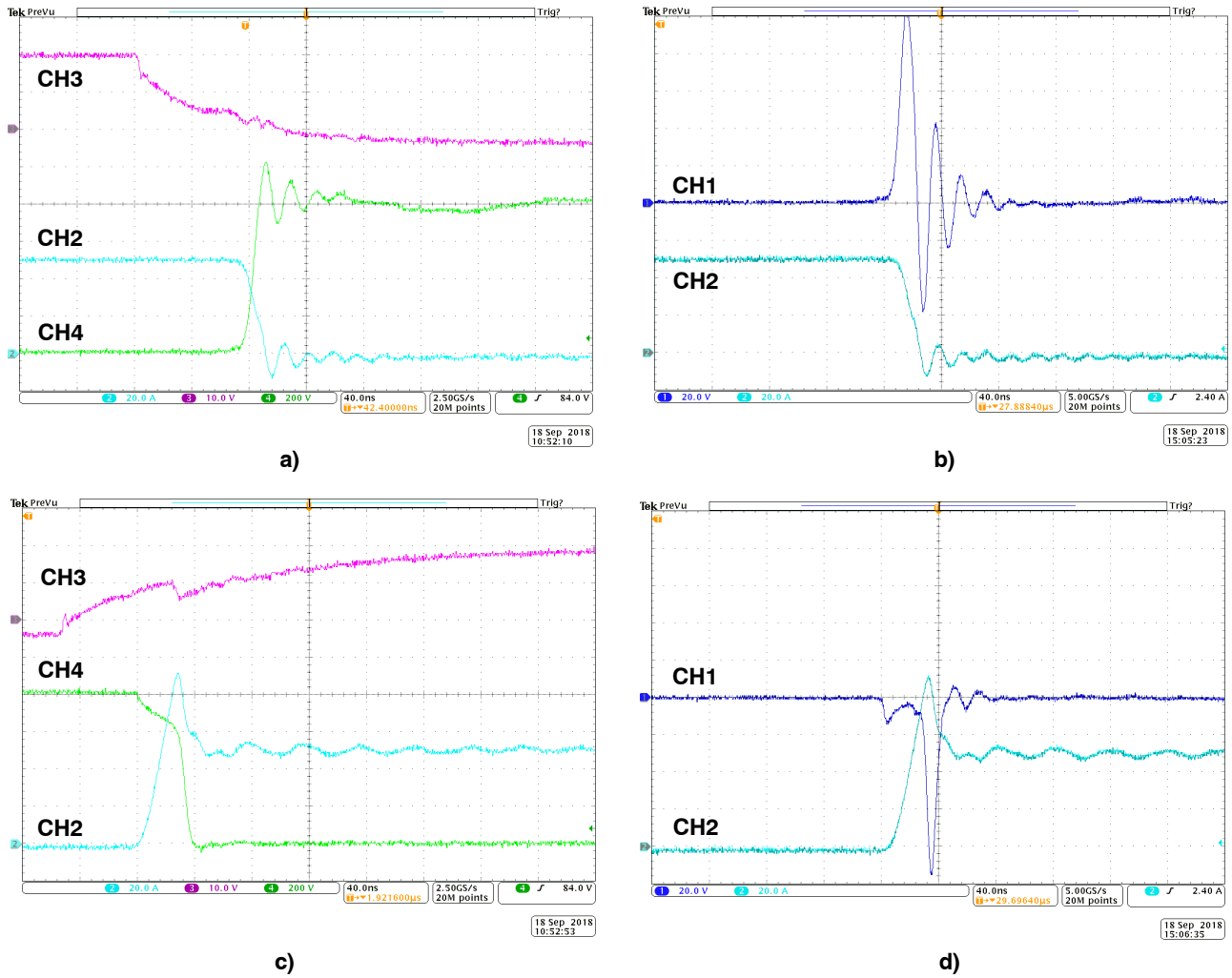


Figure 2. UF3C120040K4S Turn-off (a) and Turn-on (c) Waveforms with Snubber. Snubber Rs Voltage at Turn-Off (b), Turn-on (d). CH1: Snubber Rs Voltage (20 V/div); CH2: Drain Current (20 A/div); CH3: V_{GS} (10 V/div); CH4: V_{DS} (200 V/div). (V_{DS} 800 V, I_D 50 A, 125 °C, V_{GS} 20 V/–5 V, R_{gon} 50 Ω , R_{goff} 33 Ω , Snubber C_S 115 pF, Snubber R_S 10 Ω)

In Figure 2, experimental results of UF3C120040K4S double pulse tests shows the actual voltage across R_S at 50A load current. UF3C120040K4S [3] [4] is a 4-lead TO-247 device with kelvin-source. It is the fastest and highest efficiency series in the **onsemi** product portfolio. The R_S loss is integrated using I^2R over one switching cycle including turn-on and turn-off transients.

Figure 3 shows the comparison between measured R_S loss and conventional CV^2 estimation. The large difference stems from the fact that for inductive load turn-off transients the snubber C_S is not charging at constant voltage. The current flowing through R_S is defined by $C_S \cdot dV/dt$.

Therefore, R_S loss is load current dependent. Higher load current leads to faster dV/dt thus more current is going through R_S .

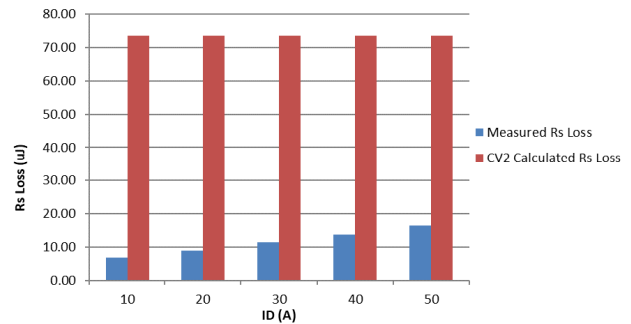
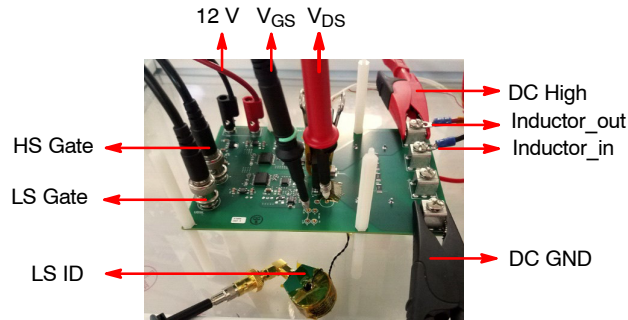


Figure 3. UF3C120040K4S Snubber R_S Loss Measurement vs. Conventional CV^2 Calculation

DOUBLE PULSE TEST (DPT) SETUP

The DPT schematic shown in Figure 1 is used to study the effect of a snubber. Snubber C_s and R_s are assembled close to high side and low side devices as shown in Figure 4. The same FET is used in the high side (HS) and low side (LS)



locations in a half-bridge configuration. Both HS and LS are heated to 125 °C by a ceramic heater. High side V_{GS} is always -5 V with the same turn-off R_g (R_{goff}) as the low side device.

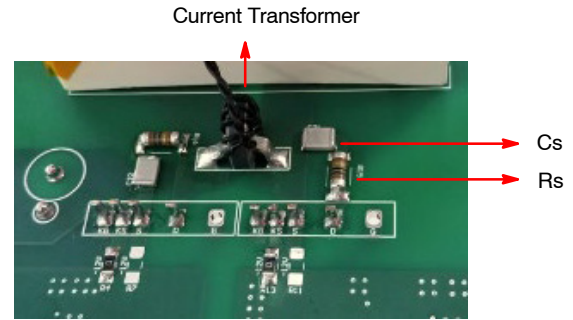


Figure 4. DPT with Side-by-side Snubber on Both High Side and Low Side Devices

All test waveforms are measured on the low side. The oscilloscope used for this test is Tektronix MDO4104B-6. V_{GS} and R_s voltage is measured with Tektronix TPP1000 1 GHz voltage probe. V_{DS} is measured with Pomona 6498 400 MHz voltage probe. DUT drain current is measured at the source using a 1:10 turn ratio transformer followed by a Pearson 2878 70 MHz Current transformer. The compact 10:1 transformer is constructed with a ferrite toroid (TC9.5/4.8/3.2-3E27) core as shown in Figure 4.

using side-by-side RC snubber is to reduce the voltage spike and ringing at high currents during the turn-off transition. As stated in section Snubber Loss this method has lower net losses than using SiC slowed by high R_{gon}/R_{goff} values. Figure 5 compares turn-on loss (E_{on}) and turn-off loss (E_{off}) of 1200 V 40 mΩ devices from three SiC FET manufacturers. As shown in Figure 1 the current measurement includes both the device drain current and the snubber current. Therefore, the loss value of UF3C120040K3S in Figure 5 includes snubber loss as well. Table 1 summarizes the testing conditions.

HARD SWITCHING EFFECT

This section explains the benefit and trade-off of using a snubber in hard switching applications. The purpose of

Table 1. DPT CONDITIONS FOR 4 SiC FET DEVICES. “X” MEANS THERE IS NO SNUBBER

Part Number	Package	V_{DS}	Temp	V_{GS}	R_{gon}/R_{goff}	R_s	C_s	C_d
UF3C120040K3S	TO-247-3L	800 V	125 °C	20 / -5 V	5 / 33 Ω	5 Ω	330 pF	0.1 μF
UF3C120040K4S	TO-247-4L	800 V	125 °C	20 / -5 V	50 / 33 Ω	10 Ω	115 pF	0.1 μF
Competitor A	TO-247-3L	800 V	125 °C	20 / -5 V	10 / 10 Ω	x	x	0.1 μF
Competitor B	TO-247-3L	800 V	125 °C	20 / -5 V	10 / 10 Ω	x	x	0.1 μF

Figure 5 shows that for TO-247-3L (3 lead) using snubber with fast switching device has lower switching loss from medium to high load. UF3C120040K4S (TO247-4L) has

the lowest switching loss because it is a 4-lead kelvin device. It also uses lower snubber C_s value.

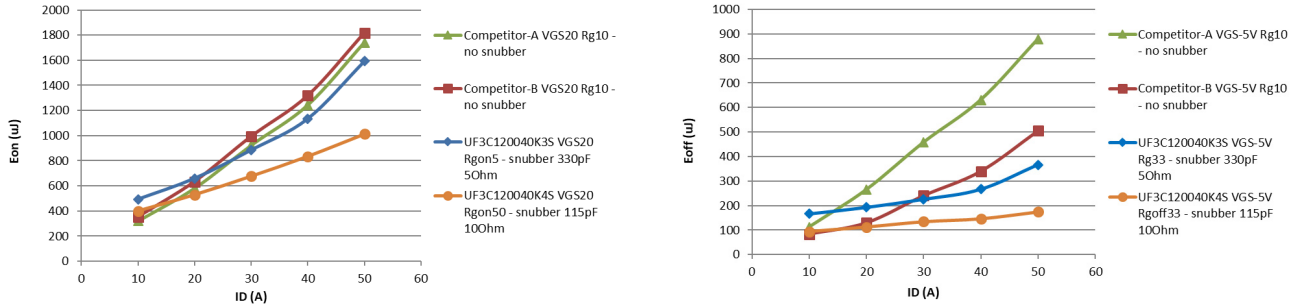


Figure 5. Hard Switching E_{on} E_{off} Comparison Among 1200 V 40 mΩ SiC Devices at V_{DS} 800 V, V_{GS} -5V

Figure 6 shows the improvement of V_{DS} and V_{GS} waveform of the fast switching SiC device (UF3C120040K3S TO247-3L) at turn-off with and without

the RC snubber. The V_{DS} spike and ringing is greatly reduced. CH1 shows the voltage across snubber Rs on the low side device.

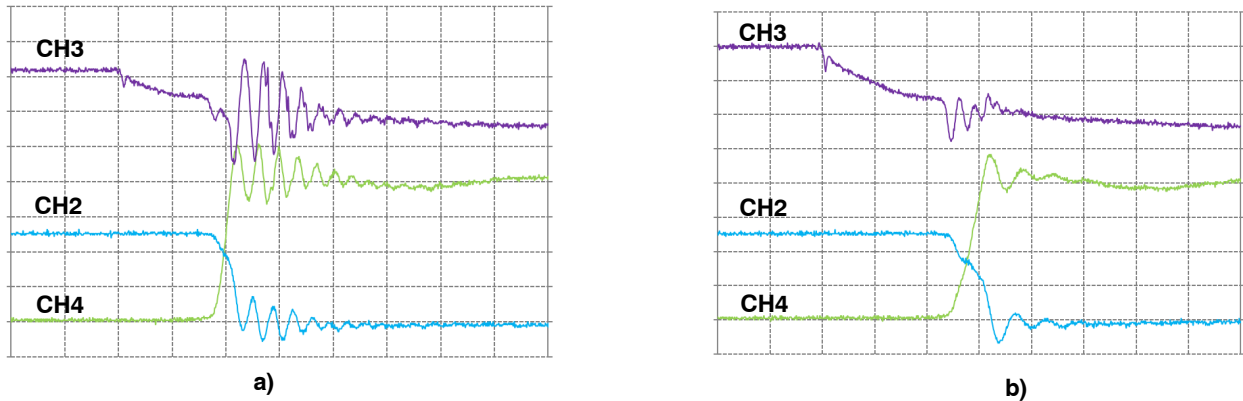


Figure 6. UF3C120040K3S Turn-Off Without Snubber (a), with Snubber (b) at V_{DS} 800 V, ID 50 A, V_{GS} -5 V, R_{goff} 33 Ω. CH2: Drain Current (20 A/div); CH3: V_{GS} (10 V/div); CH4: V_{DS} (200 V/div).

Therefore, using a fast SiC device like the UF3C series with a snubber can reduce overall loss at full load without introducing excessive voltage overshoot and ringing. The tradeoff is that snubber loss lowers light load efficiency

SOFT SWITCHING EFFECT

For soft switching applications, zero-voltage switching at turn-on during normal operation makes E_{on} negligible compared to E_{off} loss. The turn-off loss for soft switching is different from hard switching. In hard switching, part of the turn-off loss energy is stored in C_{oss} and C_s . This energy is

then dissipated in device channel during the next turn-on transient. However, in soft switching this energy is recycled and transferred to load. Therefore, the actual turn-off loss for soft switching should exclude the C_{oss} and C_s energy from hard switching turn-off loss measurement. Figure 7 compares actual turn-off loss (E_{off}) of 1200 V 40 mΩ devices from three SiC FET manufacturers. C_{oss} energy is referred to as E_{oss} . C_s energy is referred to as E_{cs} . To fully recycle the energy in C_s , the R_s for soft switching should be positioned with the power loop decoupling capacitor C_d as shown in Figure 1b.

AND90319/D

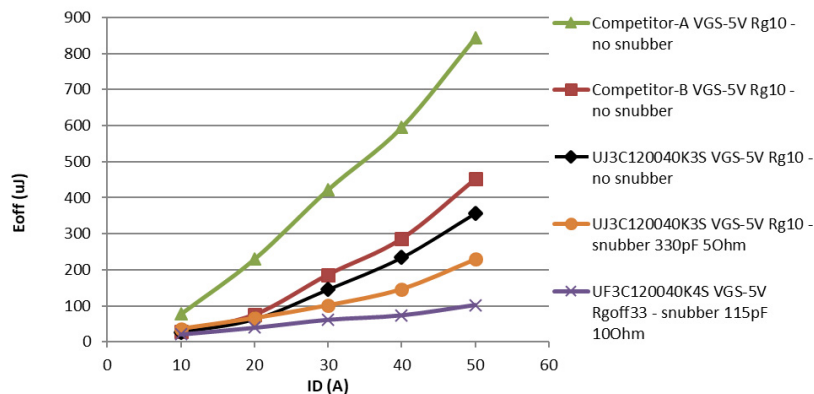


Figure 7. Soft Switching E_{off} Comparison Among 1200 V 40 mΩ SiC Devices at V_{DS} 800 V, V_{GS} -5 V
Soft Switching E_{off} is Calculated as (DPT Measured E_{off}) Minus ($E_{oss} + E_{cs}$)

The black and orange curve in Figure 7 also shows that adding snubber Cs to a half bridge will reduce soft switching turn-off loss. This is because for inductive loads the turn-off dV/dt diverts current to charge the DUT Cs, and discharge the high side Cs, diverting current from the DUT channel, and reducing the E_{off} . Adding a snubber Cs also helps designers match the circuit performance better when multiple power device suppliers are present. The tradeoff is that adding Cs would require higher minimum energy to maintain ZVS at light load.

CONCLUSION

Switching fast SiC FETs in standard TO packages requires users to either slow the FETs down, or use an RC snubber to reduce voltage overshoots and ringing. We have shown here that snubber Rs loss is much lower than the conventional $f \cdot CV^2$ estimate. We have further demonstrated that very small values of snubber capacitors can help manage the voltage overshoots, given the low C_{oss} values of

onsemi FETs. This leads to snubber losses small enough to allow regular surface mount components to be used, even when switching 50 A, 800 V per FET. Using onsemi fast devices (UF3C series) with an RC snubber enables a better trade-off in minimizing switching loss while managing turn-off voltage spikes and ringing, and is decidedly superior to just slowing devices with external gate resistors.

REFERENCES:

- [1] Maxim Integrated, "Correct Snubber Power Loss Estimate Saves the Day". [Online]. Design Solutions Power.
- [2] Link to onsemi cascode user guide: <https://www.onsemi.com/download/user-s-manual/pdf/um70114-d.pdf>
- [3] Link to Silicon Carbide (SiC) Cascode JFETs: <https://www.onsemi.com/products/discrete-power-modules/silicon-carbide-sic/silicon-carbide-sic-cascode-jfets>

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales